

# SIDC46D170H

## Fast switching diode chip in EMCON 3-Technology

## FEATURES:

- 1700V EMCON 3 technology 200 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

## This chip is used for:

EUPEC power modules



## Applications:

• resonant applications, drives

Chip Type	V <sub>R</sub>	IF	Die Size	Package	Ordering Code
SIDC46D170H	1700V	75A	6.8 x 6.8 mm <sup>2</sup>	sawn on foil	Q67050-A4175- A001

## **MECHANICAL PARAMETER:**

Raster size	6.8 x 6.8			
Area total / active	46.24 / 34.04	mm <sup>2</sup>		
Anode pad size	4.78 x 4.78			
Thickness	200			
Wafer size	150			
Flat position	180	deg		
Max. possible chips per wafer	304 pcs			
Passivation frontside	Photoimide			
Anode metallization	3200 nm Al Si Cu			
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding			
Die bond	electrically conductive glue or solder			
Wire bond	AI, ≤500µm			
Reject Ink Dot Size	Ø 0.65mm; max 1.2mm			
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C			

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## **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>		1700	V
Continuous forward current limited by $T_{j\text{max}}$	/ <sub>F</sub>		75	
Single pulse forward current (depending on wire bond configuration)	I <sub>FSM</sub>	$t_P = 10 ms sinusoidal$	430	A
Maximum repetitive forward current limited by T <sub>jmax</sub>	I <sub>FRM</sub>		150	
Operating junction and storage temperature	$T_{j}$ , $T_{stg}$		-55+150	°C

## Static Electrical Characteristics (tested on chip), $T_{j}$ =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
	-arameter Symbol C		Conditions		Тур.	max.	onne
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> =1700V	<i>T<sub>j</sub></i> =25 ° <i>C</i>			27	μA
Cathode-Anode breakdown Voltage	V <sub>Br</sub>	I <sub>R</sub> =0.25mA	<i>T<sub>j</sub></i> =25°C	1700			V
Forward voltage drop	V <sub>F</sub>	I <sub>F</sub> =75A	<i>T<sub>j</sub></i> =25°C		1.8		V

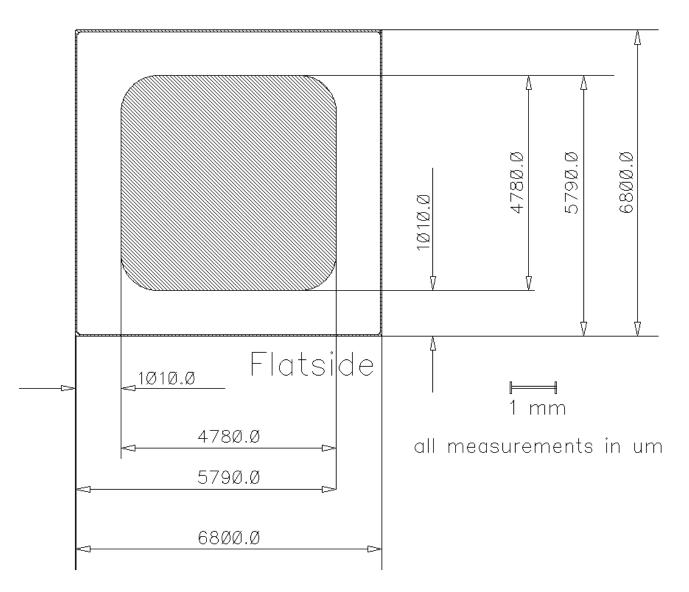
## **Dynamic Electrical Characteristics,** at $T_j$ = 25 °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
Falameter	Symbol			min.	Тур.	max.	
Peak recovery current	I <sub>RRM1</sub>	<i>I<sub>F</sub></i> =75A di/dt=920A/ <b>m</b> s	$T_j = 25 \ ^{\circ}C$		93		А
	I <sub>RRM2</sub>	$V_R = 900V$	$T_{j} = 125 \ ^{\circ}C$		100		
Reverse recovery charge	Q <sub>rr1</sub>	$I_{\rm F}=75A$	<i>T<sub>j</sub></i> =25°C		20.0		
	Q <sub>rr2</sub>	<i>di/dt=920A/ms</i> <i>V<sub>R</sub>=900V</i>	<i>T<sub>j</sub></i> =125°C		31.7		-μC
Reverse recovery energy	E <sub>rec 1</sub>	I <sub>F</sub> =75A	$T_{\rm j}=25^{\circ}C$		10.0		
	E <sub>rec2</sub>	<i>di/dt=920A/m</i> s <i>V<sub>R</sub>=900V</i>	<i>T<sub>j</sub></i> =125°C		18.3		mJ



CHIP DRAWING:

L447A1



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## FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the	INFINEON TECHNOLOGIES /	tbd
device data sheet	EUPEC	lbu

#### **Description:**

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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